

Application Serial No.: 10/780,341
Attorney Docket No.: BUR920000061US1

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AMENDMENTS TO THE CLAIMS

The status of the claims of the present application stands as follows:

Claims 1-18 (Canceled)

19. (Currently Amended) A method for scrubbing an exhaust gas of a manufacturing process, the exhaust gas comprising a first chemical component and a second chemical component, comprising the steps of:
- a. flowing the exhaust gas through an enclosure defining a chamber having a length and a central axis extending along said length and containing at least one-a plurality of substrates spaced from one another along said length and oriented substantially perpendicular to said central axis;
 - b. baffling, using said at least one-by said plurality of substrates, the exhaust gas within said chamber so as to increase the residence time of the exhaust gas within said chamber; and
 - c. causing the first chemical component to be chemical vapor deposited onto ones of said at least oneplurality of substrates.
20. (Previously Presented) A method according to claim 19, further comprising the step of removing the second chemical component from the exhaust gas after performing step c).
21. (Currently Amended) A method according to claim 19, wherein step c) is performed by heating at least one of (1) said at least oneplurality of substrates and (2) said enclosure to at least 800°C.
22. (Currently Amended) A method according to claim 21, wherein step c) is performed by heating at least one of (1) said at least oneplurality of substrates and (2) said enclosure to at least 1100°C.

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23. **(Original)** A method according to claim 19, wherein the first chemical component is non-toxic and the second chemical component is toxic.
24. **(Original)** A method according to claim 23, wherein the first chemical component comprises silicon and the second chemical component comprises arsenic.
25. **(Previously Presented)** A method according to claim 19, further comprising after step c) the steps of:
- a. removing said at least one substrate from said enclosure;
 - b. cleaning said at least one substrate of any film deposited thereon;
 - c. installing said at least one substrate in said enclosure; and
 - d. again causing the first chemical component to be chemical vapor deposited onto said at least one substrate.
26. **(Currently Amended)** A method of scrubbing an exhaust gas of a manufacturing process, the exhaust gas comprising a carrier gas and an n-type dopant gas, the carrier gas comprising a component depositable by chemical vapor deposition, the method comprising the steps of:
- a. flowing the exhaust gas through an enclosure defining a chamber having a length and a central axis extending along said length and containing a plurality of substrates spaced from one another along said length and oriented substantially perpendicular to said central axis;
 - b. baffling, using said at least one by said plurality of substrates, the exhaust gas within said chamber so as to increase the residence time of the exhaust gas within said chamber; and
 - c. causing an n-doped-a layer of silicon the component of the carrier gas to be chemical vapor deposited onto ones of said at least one plurality of substrates.

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27. **(Currently Amended)** A method according to claim 26, further comprising the step of removing the n-type-dopant gas from the exhaust gas after performing step c).
28. **(Currently Amended)** A method according to claim 26, wherein step c) is performed by heating at least one of (1) said at least one plurality of substrates and (2) said enclosure to at least 800°C.
29. **(Currently Amended)** A method according to claim 28, wherein step c) is performed by heating at least one of (1) said at least one plurality of substrates and (2) said enclosure to at least 1100°C.
30. **(Currently Amended)** A method according to claim 26, wherein the carrier gas comprises silicon and the n-type-dopant gas comprises arsenic.
31. **(Canceled)**
32. **(Previously Presented)** A method according to claim 26, wherein said enclosure contains a plurality of substrates arranged in series with one another along said chamber so as to baffle flow of the exhaust gas.
33. **(Currently Amended)** A method according to claim 3226, wherein said plurality of substrates are arranged within said chamber so as to cause the exhaust gas to flow along a substantially serpentine path within said chamber.
34. **(Currently Amended)** A method according to claim 3226, wherein each of said plurality of substrates comprises a plurality of apertures and step b) is performed by causing the exhaust gas to flow substantially only through said plurality of apertures of each of said plurality of substrates.

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35. (Currently Amended) A method according to claim 19, wherein each of said at least one plurality of substrates has a plurality of apertures and step b) is performed by causing the exhaust gas to flow substantially only through said plurality of apertures.

36. (Cancelled)

37. (Currently Amended) A method according to claim 3619, wherein said plurality of substrates are arranged within said chamber so as to cause the exhaust gas to flow along a substantially serpentine path within said chamber.

38. (Currently Amended) A method according to claim 3619, wherein each of said plurality of substrates comprises a plurality of apertures and step b) is performed by causing the exhaust gas to flow substantially only through said plurality of apertures of each of said plurality of substrates.